

In the claims

- 1-5 (withdrawn)
- 6-11 (canceled)
12. (currently amended) A method of endpoint detection in plasma etching of a target layer of material, comprising the actions of:
- providing a target layer of material of which not less than 90% of the target layer surface is covered with a mask;
- etching the less than 10% open area of the target layer uncovered by the mask;
- measuring voltage across a plasma system by measuring a voltage across an element that is external to said plasma system;
- detecting a change of the voltage prior to the completion of the etching of the target layer of material; and
- stopping etch when said voltage decreases a predetermined amount within a predetermined time.
13. (original) The method of Claim 12, wherein said element is a resistor.
14. (original) The method of Claim 12, wherein said voltage is a DC voltage.
- 15-18. (canceled)
19. (previously added) The method of claim 12, wherein the element is part of an impedance matching network.
20. (new) The method of claim 12, wherein the not less than 90% of the target layer surface is not less than 96%.
21. (new) The method of claim 12, wherein the not less than 90% of the target layer surface is not less than 99%.